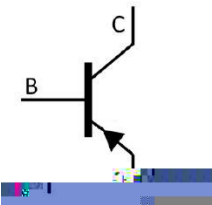


WR0<5 SQS Silicon PNP transistor in a TO-92 Plastic Package.

NVG4949+D,
Complementary pair with KSD1616(A).

/
Audio frequency power amplifier, medium speed switching.



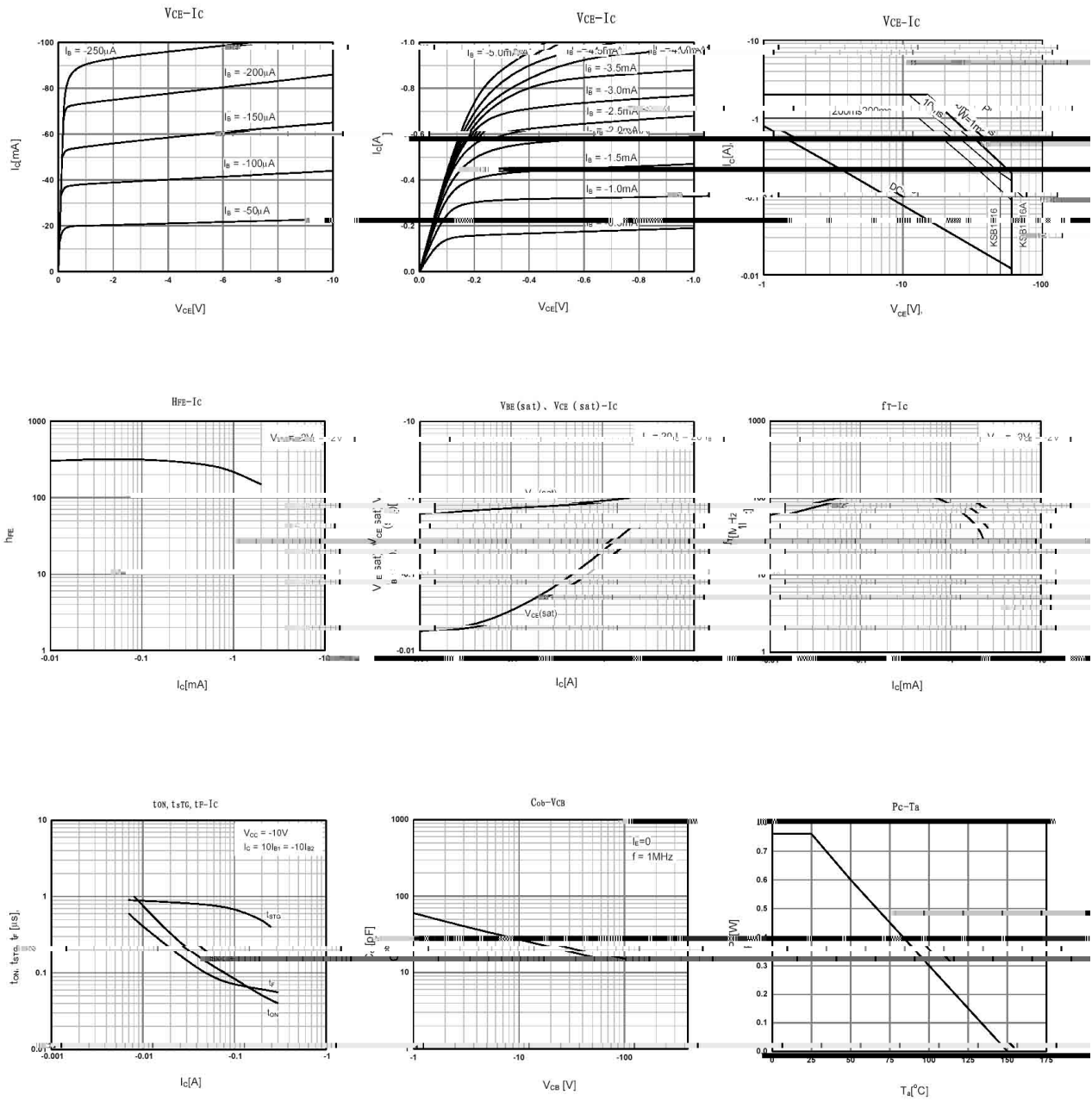
PIN1	Base	PIN 2	Collector	PIN 3	Emitter
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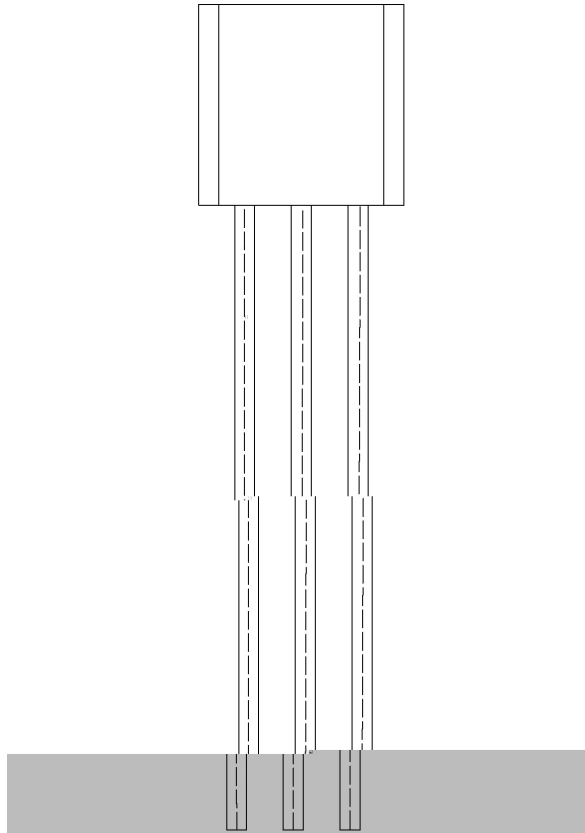
Parameter	Symbol		Rating	Unit
Collector to Base Voltage	V_{CBO}	KSB1116	-60	V
		KSB1116A	-120	
Collector to Emitter Voltage	V_{CEO}	KSB1116	-50	V
		KSB1116A	-60	
Emitter to Base Voltage	V_{EBO}		-6.0	V
Collector Current - Continuous	I_C		-1.0	A
Base Current – Continuous	I_B		-2.0	A
Collector Power Dissipation	P_C		750	mW
Junction Temperature	T_j		150	
Storage Temperature Range	T_{stg}		-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-60V$ $I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-6.0V$ $I_C=0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$	KSB1116 $V_{CE}=-2.0V$ $I_C=-100mA$	135		600	

/ Electrical Characteristic Curve

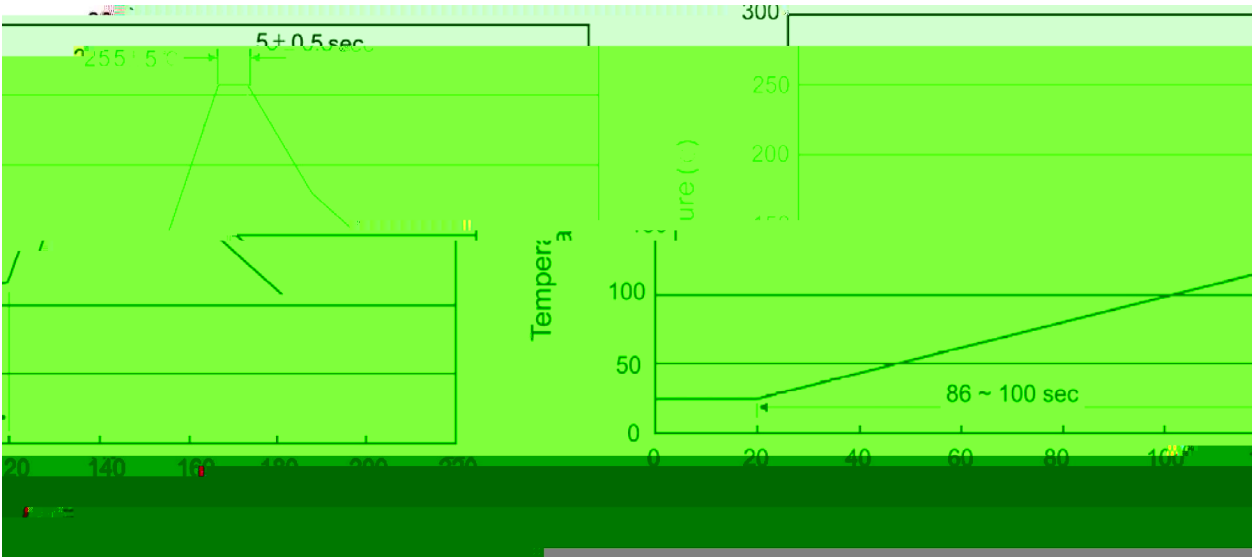


/ Marking Instructions



EU:-
E4449

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|--------|------|-----------|--------|---|
| 1 | 25 | 150% | 60 | 90sec; | 1.Preheating:25~150%, Time:60~90sec. |
| 2 | 255±5% | | 5±0.5sec; | | 2.Peak Temp.:255±5%, Duration:5±0.5sec. |
| 3 | | 2 | 10%/sec. | | 3. Cooling Speed: 2~10%/sec. |

/ Resistance to Soldering Heat Test Conditions

270±5%	10±1 sec.	Temp:270±5	Time:10±1 sec
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/ Packaging SPEC.

/ BULK

Package Type	Units	Dimension	314	0
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